Inverter

Rev. 2 — 18 November 2013

Product data sheet

1. General description

The 74HC3G04-Q100; 74HCT3G04-Q100 is a triple inverter. Inputs include clamp diodes that enable the use of current limiting resistors to interface inputs to voltages in excess of V_{CC} .

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade at 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - ◆ Specified from -40 °C to +85 °C and from -40 °C to +125 °C
- Input levels:
 - For 74HC3G04-Q100: CMOS level
 - For 74HCT3G04-Q100: TTL level
- Wide supply voltage range from 2.0 V to 6.0 V
- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- Multiple package options
- ESD protection:
 - MIL-STD-883, method 3015 exceeds 2000 V
 - HBM JESD22-A114F exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)



3. Ordering information

Table 1. Ordering information								
Type number	Package							
	Temperature range Name		Description	Version				
74HC3G04DP-Q100	–40 °C to +125 °C	TSSOP8	plastic thin shrink small outline package; 8 leads;	SOT505-2				
74HCT3G04DP-Q100			body width 3 mm; lead length 0.5 mm					
74HC3G04DC-Q100	–40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8	SOT765-1				
74HCT3G04DC-Q100			leads; body width 2.3 mm					
74HC3G04GD-Q100	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package;	SOT996-2				
74HCT3G04GD-Q100			no leads; 8 terminals; body $3 \times 2 \times 0.5$ mm					

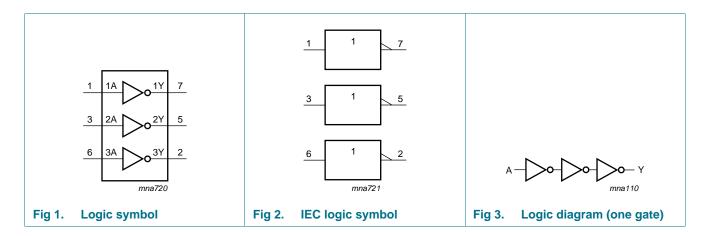
4. Marking

.. ..

Table 2. Marking codes	
Type number	Marking code ^[1]
74HC3G04DP-Q100	H04
74HCT3G04DP-Q100	T04
74HC3G04DC-Q100	H04
74HCT3G04DC-Q100	T04
74HC3G04GD-Q100	H04
74HCT3G04GD-Q100	T04

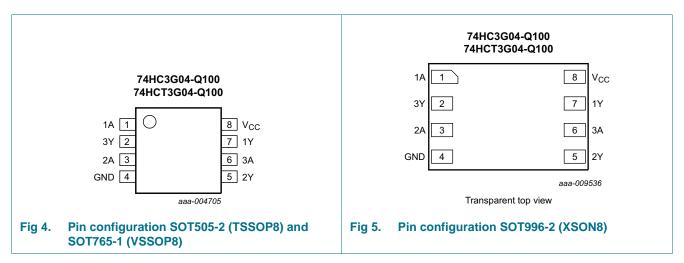
[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram



6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3. Pin description							
Symbol	Pin	Description					
1A, 2A, 3A	1, 3, 6	data input					
GND	4	ground (0 V)					
1Y, 2Y, 3Y	7, 5, 2	data output					
V _{CC}	8	supply voltage					

7. Functional description

Table 4.Function table^[1]

Input	Output
nA	nY
L	Н
Н	L

[1] H = HIGH voltage level; L = LOW voltage level.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7.0	V
I _{IK}	input clamping current	$V_{\rm I}$ < –0.5 V or $V_{\rm I}$ > $V_{\rm CC}$ + 0.5 V	<u>[1]</u> _	±20	mA
I _{OK}	output clamping current	$V_{\rm O}$ < –0.5 V or $V_{\rm O}$ > $V_{\rm CC}$ + 0.5 V	<u>[1]</u> _	±20	mA
Ι _Ο	output current	$V_{O} = -0.5 \text{ V}$ to ($V_{CC} + 0.5 \text{ V}$)	<u>[1]</u> _	25	mA
I _{CC}	supply current		<u>[1]</u> _	50	mA
I _{GND}	ground current		<u>[1]</u> –50	-	mA
T _{stg}	storage temperature		-65	+150	°C
PD	dynamic power dissipation	T_{amb} = -40 °C to +125 °C	[2] _	300	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For TSSOP8 package: above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K. For VSSOP8 package: above 110 °C the value of P_{tot} derates linearly with 8 mW/K. For XSON8 package: above 45 °C the value of P_{tot} derates linearly with 2.4 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	bol Parameter Condition		74HC3G04-Q100			74H0	Unit		
		Min	Тур	Max	Min	Тур	Max	_	
V _{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	V _{CC}	0	-	V _{CC}	V
Vo	output voltage		0	-	V _{CC}	0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
Δt/ΔV	input transition rise	$V_{CC} = 2.0 V$	-	-	625	-	-	-	ns/V
	and fall rate	$V_{CC} = 4.5 V$	-	1.67	139	-	1.67	139	ns/V
		$V_{CC} = 6.0 V$	-	-	83	-	-	-	ns/V

10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V). All typical values are measured at T_{amb} = 25 °C.

Symbol	Parameter	Conditions		25 °C		–40 °C t	o +85 °C	-40 °C t	to +125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
74HC3G	04-Q100	1								
VIH	HIGH-level	V _{CC} = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
	input voltage	$V_{CC} = 4.5 V$	3.15	2.4	-	3.15	-	3.15	-	V
		V _{CC} = 6.0 V	4.2	3.2	-	4.2	-	4.2	-	V
V _{IL}	LOW-level	V _{CC} = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
	input voltage	$V_{CC} = 4.5 V$	-	2.1	1.35	-	1.35	-	1.35	V
		V _{CC} = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V
0.11	HIGH-level	$V_{I} = V_{IH} \text{ or } V_{IL}$								
	output voltage	$I_0 = -20 \ \mu A; \ V_{CC} = 2.0 \ V$	1.9	2.0	-	1.9	-	1.9	-	V
		$I_O = -20 \ \mu\text{A}; \ V_{CC} = 4.5 \ \text{V}$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_0 = -20 \ \mu A; \ V_{CC} = 6.0 \ V$	5.9	6.0	-	5.9	-	5.9	-	V
		I_{O} = -4.0 mA; V_{CC} = 4.5 V	4.18	4.32	-	4.13	-	3.7	-	V
		$I_{O} = -5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.68	5.81	-	5.63	-	5.2	-	V
V _{OL}	LOW-level	$V_{I} = V_{IH} \text{ or } V_{IL}$								
	output voltage	$I_0 = 20 \ \mu A; \ V_{CC} = 2.0 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_0 = 20 \ \mu A; \ V_{CC} = 4.5 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_0 = 20 \ \mu A; \ V_{CC} = 6.0 \ V$	-	0	0.1	-	0.1	-	0.1	V
		I_{O} = 4.0 mA; V_{CC} = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
		$I_0 = 5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.26	-	0.33	-	0.4	V
1	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0$ V	-	-	±0.1	-	±1.0	-	±1.0	μA
СС	supply current	per input pin; $V_{CC} = 6.0 \text{ V};$ $V_I = V_{CC} \text{ or GND}; I_O = 0 \text{ A};$	-	-	1.0	-	10	-	20	μA
Cı	input capacitance		-	1.5	-	-	-	-	-	pF

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Symbol	Parameter	Conditions		25 °C		–40 °C t	o +85 °C	-40 °C t	o +125 °C	Unit
•			Min	Тур	Max	Min	Max	Min	Max	
74HCT3	G04-Q100			I				I		
V _{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
V _{IL}	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
V _{OH}	HIGH-level	$V_{I} = V_{IH} \text{ or } V_{IL}$								
output voltage	$I_O = -20 \ \mu\text{A}; \ V_{CC} = 4.5 \ \text{V}$	4.4	4.5	-	4.4	-	4.4	-	V	
		I_{O} = -4.0 mA; V_{CC} = 4.5 V	4.18	4.32	-	4.13	-	3.7	-	V
V _{OL}	V _{OL} LOW-level	$V_{I} = V_{IH} \text{ or } V_{IL}$								
	output voltage	$I_0 = 20 \ \mu A; \ V_{CC} = 4.5 \ V$	-	0	0.1	-	0.1	-	0.1	V
		I_{O} = 4.0 mA; V_{CC} = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
I	input leakage current	V_{I} = V_{CC} or GND; V_{CC} = 5.5 V	-	-	±0.1	-	±1.0	-	±1.0	μΑ
I _{CC}	supply current	per input pin; $V_{CC} = 5.5 V$; $V_I = V_{CC}$ or GND; $I_O = 0 A$;	-	-	1.0	-	10	-	20	μΑ
ΔI_{CC}	additional supply current	per input; $V_{CC} = 4.5 V \text{ to } 5.5 V;$ $V_I = V_{CC} - 2.1 V; I_O = 0 A$	-	-	300	-	375	-	410	μΑ
CI	input capacitance		-	1.5	-	-	-	-	-	рF

Table 7. Static characteristics ...continued

Voltages are referenced to GND (ground = 0 V). All typical values are measured at T_{amb} = 25 °C.

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); all typical values are measured at $T_{amb} = 25$ °C; for test circuit, see Figure 7.

Symbol	Parameter	Conditions			25 °C		–40 °C t	o +85 °C	–40 °C t	o +125 °C	Unit
				Min	Тур	Max	Min	Max	Min	Max	
74HC3G	04-Q100										
	propagation	nA to nY; see Figure 6	[1]								
	delay	$V_{CC} = 2.0 V$		-	22	75	-	90	-	110	ns
		$V_{CC} = 4.5 V$		-	8	15	-	18	-	22	ns
		$V_{CC} = 6.0 V$		-	6	13	-	16	-	20	ns
t _t	transition	see Figure 6	[2]								
	time	$V_{CC} = 2.0 V$		-	18	75	-	95	-	125	ns
		$V_{CC} = 4.5 V$		-	6	15	-	19	-	25	ns
		$V_{CC} = 6.0 V$		-	5	13	-	16	-	20	ns
C _{PD}	power dissipation	$V_{I} = GND$ to V_{CC}	[3]	-	9	-	-	-	-	-	pF

capacitance

Inverter

Table 8. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); all typical values are measured at $T_{amb} = 25 \text{ °C}$; for test circuit, see Figure 7.

Symbol	Parameter	Conditions		25 °C		–40 °C to +85 °C		–40 °C to +125 °C		Unit	
			Min	Тур	Max	Min	Max	Min	Max		
74HCT3	G04-Q100										
t _{pd}		nA to nY; see Figure 6	[1]								
	delay	$V_{CC} = 4.5 V$		-	10	18	-	23	-	29	ns
t _t	transition time	V_{CC} = 4.5 V; see <u>Figure 6</u>	[2]	-	6	15	-	19	-	22	ns
C _{PD}	power dissipation capacitance	$V_{\rm I}$ = GND to V_{CC} – 1.5 V	<u>[3]</u>	-	9	-	-	-	-	-	pF

[1] t_{pd} is the same as t_{PLH} and t_{PHL} .

- [2] t_t is the same as t_{TLH} and t_{THL} .
- [3] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

 $P_{D} = C_{PD} \times V_{CC}{}^{2} \times f_{i} \times N + \Sigma (C_{L} \times V_{CC}{}^{2} \times f_{o}) \text{ where:}$

 f_i = input frequency in MHz;

 f_o = output frequency in MHz;

 C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}{}^2 \times f_o) = \text{sum of outputs.}$

12. Waveforms

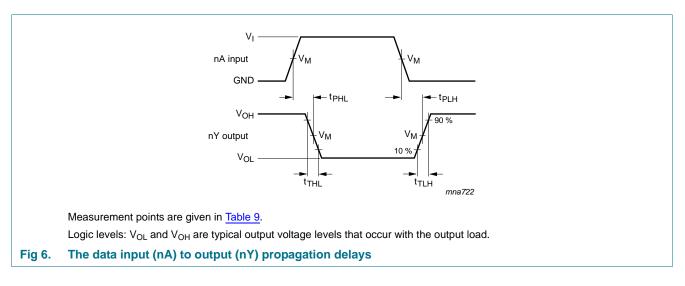


Table 9. Measurement points

Туре	Input	Output
	V _M	V _M
74HC3G04-Q100	$0.5 imes V_{CC}$	$0.5 \times V_{CC}$
74HCT3G04-Q100	1.3 V	1.3 V

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74HC3G04-Q100; 74HCT3G04-Q100

Inverter

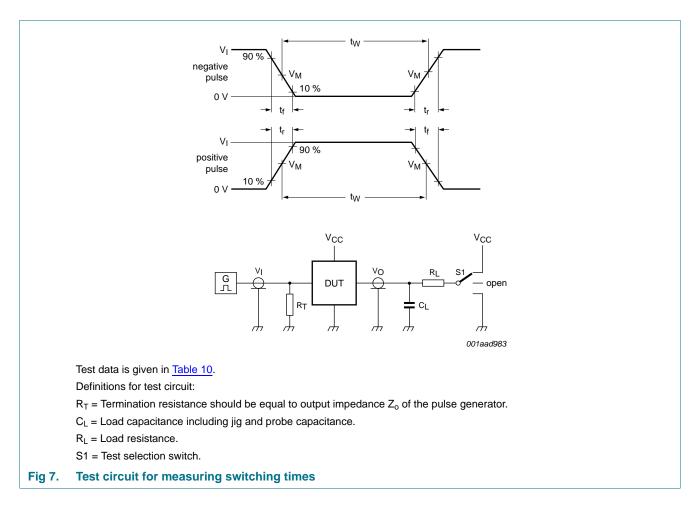


Table 10. Test data

Туре	Input		Load		S1 position
	VI	t _r , t _f	CL	RL	t _{PHL} , t _{PLH}
74HC3G04-Q100	V _{CC}	≤ 6 ns	50 pF	1 kΩ	open
74HCT3G04-Q100	3 V	\leq 6 ns	50 pF	1 kΩ	open

13. Package outline

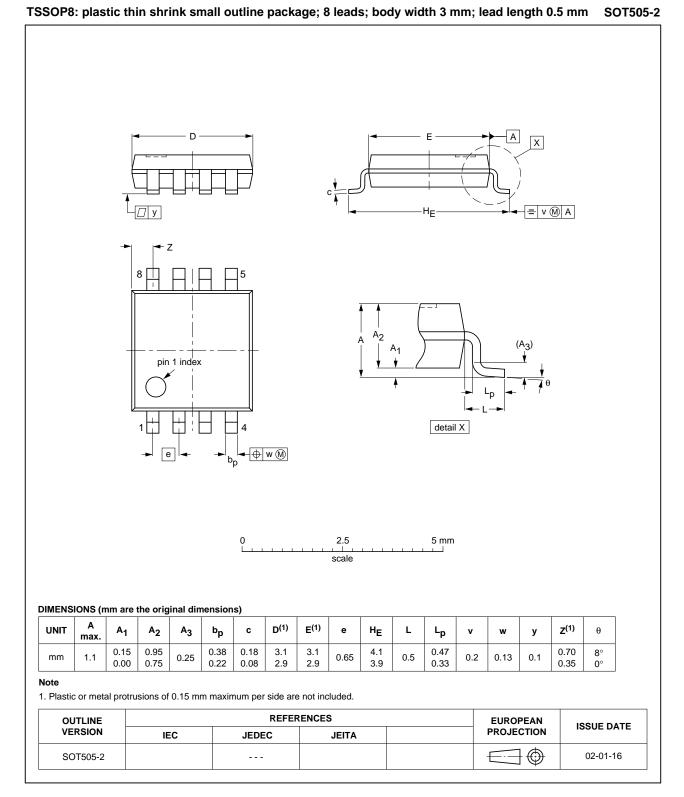


Fig 8. Package outline SOT505-2 (TSSOP8)

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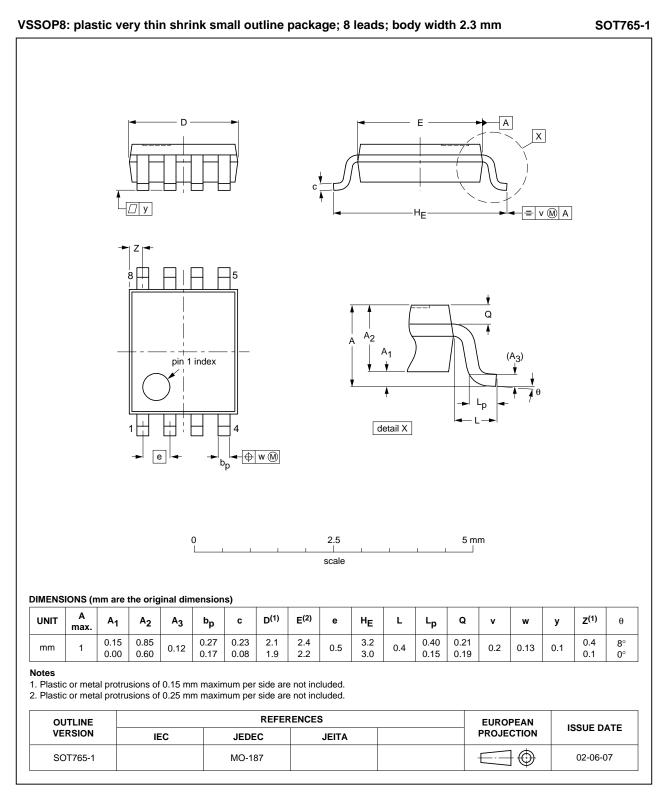
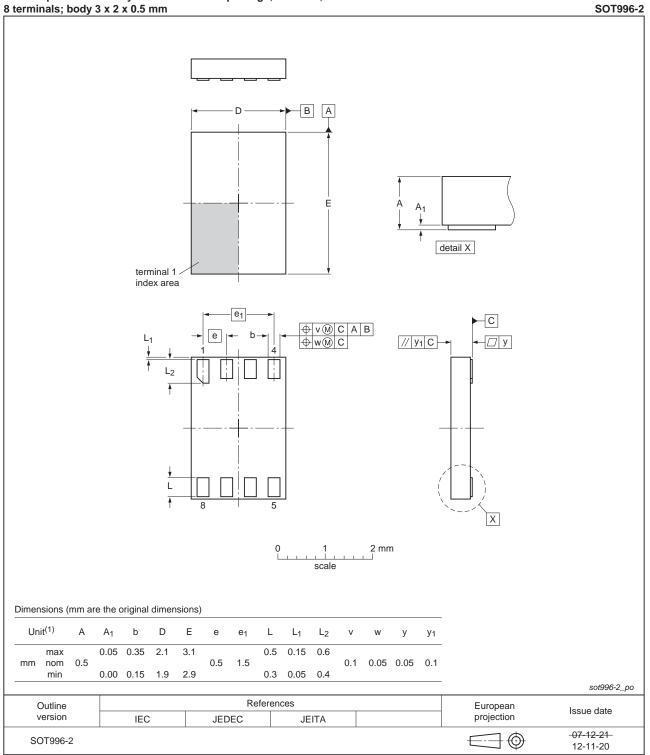


Fig 9. Package outline SOT765-1 (VSSOP8)

Inverter



XSON8: plastic extremely thin small outline package; no leads;

Fig 10. Package outline SOT996-2 (XSON8)

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74HC_HCT3G04_Q100

А

14. Abbreviations

AcronymDescriptionCMOSComplementary Metal-Oxide SemiconductorDUTDevice Under TestESDElectroStatic DischargeHBMHuman Body ModelMILMilitaryMMMachine ModelTTLTransistor-Transistor Logic	Table 11.	Abbreviations	
DUTDevice Under TestESDElectroStatic DischargeHBMHuman Body ModelMILMilitaryMMMachine Model	Acronym		Description
ESD ElectroStatic Discharge HBM Human Body Model MIL Military MM Machine Model	CMOS		Complementary Metal-Oxide Semiconductor
HBM Human Body Model MIL Military MM Machine Model	DUT		Device Under Test
MIL Military MM Machine Model	ESD		ElectroStatic Discharge
MM Machine Model	HBM		Human Body Model
	MIL		Military
TTL Transistor-Transistor Logic	MM		Machine Model
	TTL		Transistor-Transistor Logic

15. Revision history

Table 12.Revision history				
Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT3G04_Q100 v.2	20131118	Product data sheet	-	74HC_HCT3G04_Q100 v.1
Modifications:	 Added type package) 	numbers 74HC3G04GD-0	Q100 and 74HCT3	G04GD-Q100 (XSON8
74HC_HCT3G04_Q100 v.1	20120827	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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